

GE2026

NPN EPITAXIAL PLANAR TRANSISTOR

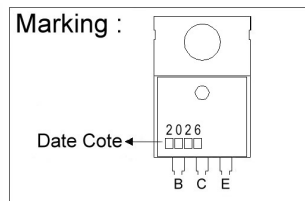
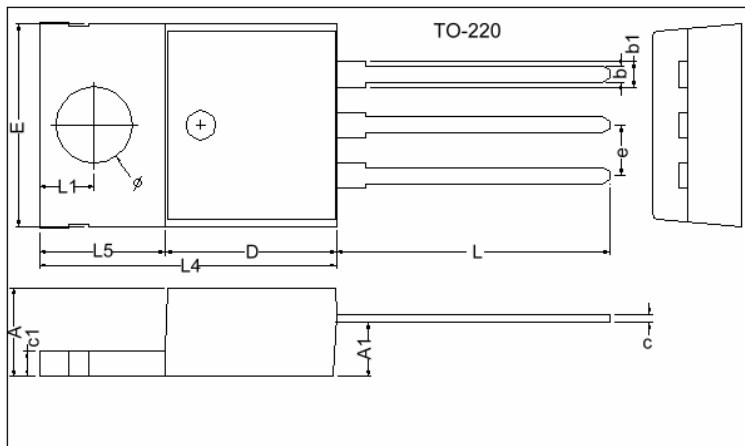
Description

The GE2026 is designed for general purpose application.

Features

- Low Collector Saturation Voltage : $V_{CE(sat)} = 1.0V$ (Max.) @ $I_C=2A$, $I_B=0.2A$,

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.40	4.80	c1	1.25	1.45
b	0.76	1.00	b1	1.17	1.47
c	0.36	0.50	L	13.25	14.25
D	8.60	9.00	e	2.54 REF.	
E	9.80	10.4	L1	2.60	2.89
L4	14.7	15.3	Ø	3.71	3.96
L5	6.20	6.60	A1	2.60	2.80

Absolute Maximum Ratings ($T_A=25^{\circ}C$)

Parameter		Symbol	Ratings	Unit
Collector to Base Voltage		V_{CBO}	60	V
Collector to Emitter Voltage		V_{CEO}	60	V
Emitter to Base Voltage		V_{EBO}	7	V
Collector Current		I_C	3	A
Base Current		I_B	0.5	A
Total Device Dissipation	$T_A=25^{\circ}C$	P_D	2	W
	$T_C=25^{\circ}C$	P_D	20	W
Junction Temperature		T_J	150	$^{\circ}C$
Storage Temperature		T_{stg}	-55 ~ +150	$^{\circ}C$

Electrical Characteristics ($T_A = 25^{\circ}C$ unless otherwise noted)

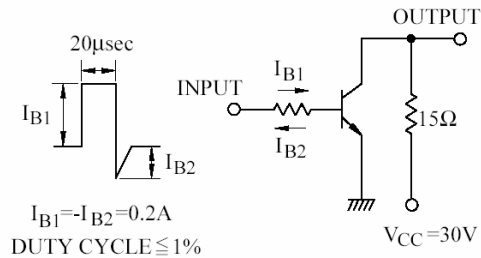
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	60	-	-	V	$I_C=100\mu A$, $I_E=0$
BV_{CEO}	60	-	-	V	$I_C=50mA$, $I_B=0$
BV_{EBO}	7	-	-	V	$I_E=100\mu A$, $I_C=0$
I_{CBO}	-	-	100	μA	$V_{CB}=60V$, $I_E=0$
I_{EBO}	-	-	100	μA	$V_{EB}=7V$, $I_C=0$
* $V_{CE(sat)}$	-	-	1.0	V	$I_C=2A$, $I_B=0.2A$
* $V_{BE(on)}$	-	-	1.0	V	$V_{CE}=5V$, $I_C=0.5A$
* h_{FE1}	100	-	320		$V_{CE}=5V$, $I_C=0.5A$
* h_{FE2}	20	-	-		$V_{CE}=5V$, $I_C=3A$
f_T	-	30	-	MHz	$V_{CE}=5V$, $I_C=0.5A$
C_{ob}	-	35	-	pF	$V_{CB}=10V$, $I_E=0$, $f=1MHz$
t_{on} (Turn-on Time)	-	0.65	-	uS	See specified test circuit
t_{stg} (Storage Time)	-	1.3	-		
t_f (Fall Time)	-	0.65	-		

*Pulse Test: Pulse Width $\leq 380\mu s$, Duty Cycle $\leq 2\%$

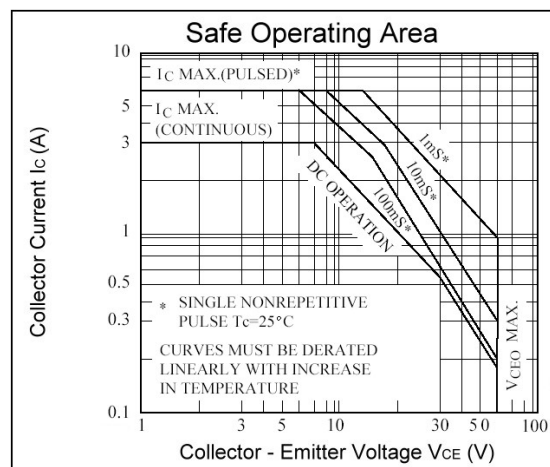
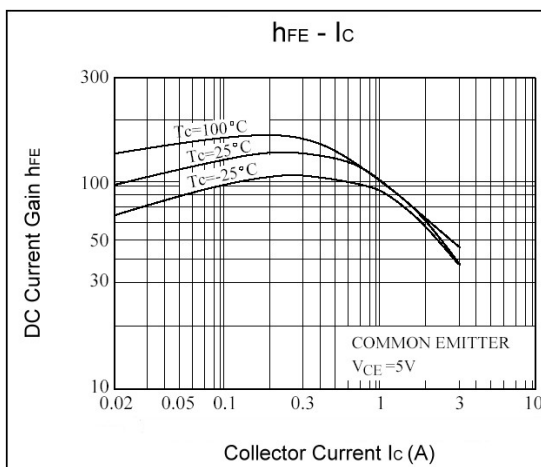
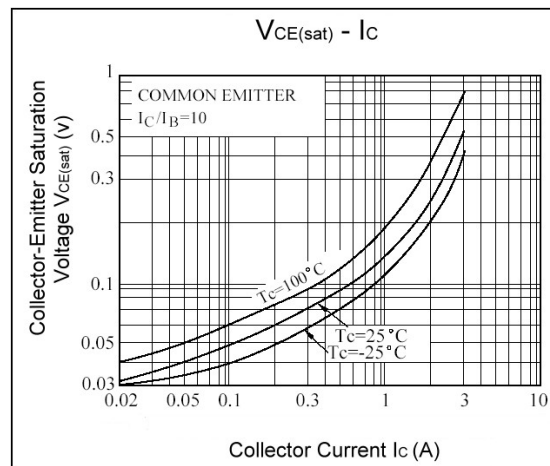
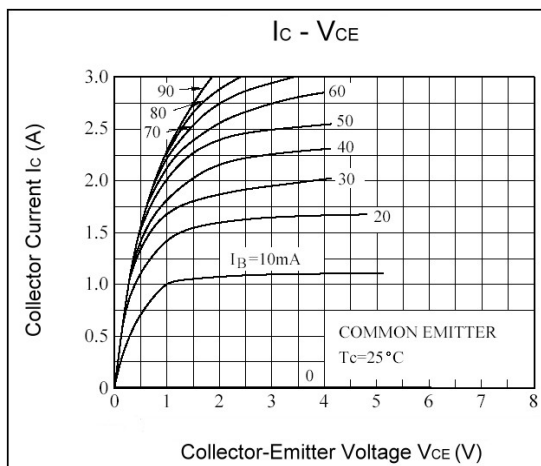
Classification Of hFE1

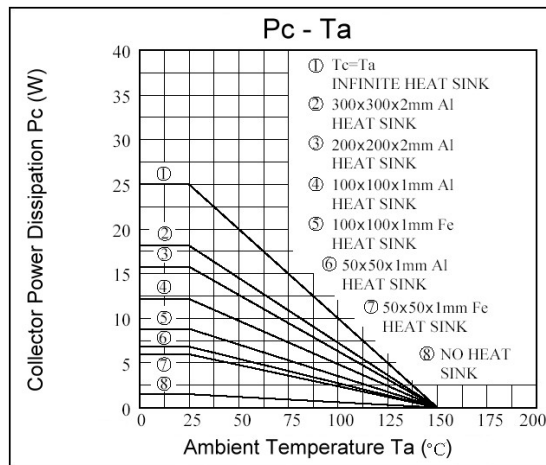
Rank	Y	GR
Range	100 - 200	160 - 320

Switching Time Test Circuit



Characteristics Curve





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Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165